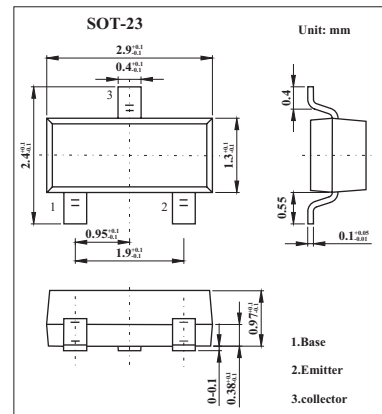


FMMT596

■ Features

- SOT23 PNP silicon planar



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-220	V
Collector-emitter voltage	V _{CEO}	-200	V
Emitter-base voltage	V _{EBO}	-5	V
Peak collector current	I _{CM}	-1	A
Collector current	I _C	-0.3	A
Base current	I _B	-200	mA
Power dissipation	P _{tot}	500	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-220			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=-10mA	-200			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5			V
Collector cutoff current	ICBO	VCB=-200V			-100	nA
Collector-Emitter Cut-Off Current	ICES	VCE=-200V			-100	nA
Emitter cut-off current	IEBO	VEB=-4V			-100	nA
Collector-emitter saturation voltage *	VCE(sat)	IC=-100mA, IB=-10mA			-0.2	V
		IC=-250mA, IB=-25mA			-0.35	V
Base-emitter saturation voltage *	VBE(sat)	IC=-250mA, IB=-25mA			-1.0	V
Base-emitter voltage *	VBE(ON)	IC=-250mA, VCE=-10V			-0.9	V
Static Forward Current Transfer Ratio	hFE	IC=-1mA, VCE=-10V	100			
		IC=-100mA, VCE=-10V*	100			
		IC=-250mA, VCE=-10V*	85		300	
		IC=-400mA, VCE=-10V*	35			
Current-gain-bandwidth product	fT	IC=-50mA, VCE=-10V, f=100MHz	150			MHz
Output capacitance	Cobo	VCB=-10V, f=1MHz			10	pF

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	596
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